

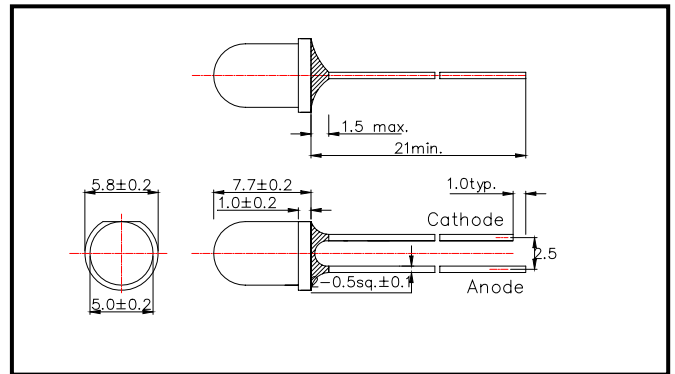
L750-04AU Infrared LED Lamp

L750-04AU is an AlGaAs LED mounted on a lead frame with a clear epoxy lens. On forward bias it emits a spectral band of radiation, which peaks at 750nm.

◆ Specifications

- | | |
|---------------------|--------------------|
| 1) Product Name | Infrared LED Lamp |
| 2) Type No. | L750-04AU |
| 3) Chip | |
| (1) Chip Material | AlGaAs |
| (2) Peak Wavelength | 750nm typ. |
| 4) Package | |
| (1) Type | Φ5mm clear molding |
| (2) Resin Material | Epoxy Resin |
| (3) Lead Frame | Soldered |

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	200	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	500	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +85	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	260	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =50mA		1.85	2.00	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =50mA	13.0	18.0		mW
Radiant Intensity	I _E	I _F =50mA	18	35		mW/sr
Peak Wavelength	λ _P	I _F =50mA	730	750	770	nm
Half Width	Δλ	I _F =50mA		30		nm
Viewing Half Angle	θ _{1/2}	I _F =50mA		±20		deg.
Rise Time	t _r	I _F =50mA		80		ns
Fall Time	t _f	I _F =50mA		80		ns.

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.